R1LV0414C-I Series

Wide Temperature Range Version
4M SRAM (256-kword × 16-bit)

REJ03C0196-0201
Rev. 2.01
Nov.24.2005

Description

The R1LV0414C-I is a 4-Mbit static RAM organized 256-kword × 16-bit. R1LV0414C-I Series has realized higher density, higher performance and low power consumption by employing CMOS process technology (6-transistor memory cell). The R1LV0414C-I Series offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It has packaged in 44-pin TSOP II.

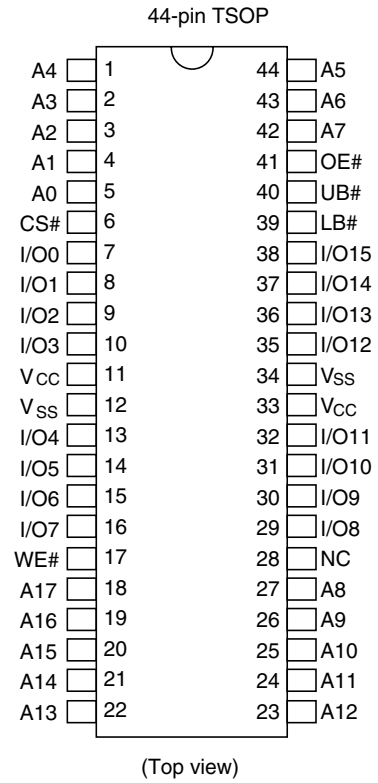
Features

- Single 2.5 V and 3.0 V supply: 2.2 V to 3.6 V
- Fast access time: 55/70 ns (max)
- Power dissipation:
  - Active: 5.0 mW/MHz (typ)(V_{CC} = 2.5 V)
    : 6.0 mW/MHz (typ) (V_{CC} = 3.0 V)
  - Standby: 1.25 µW (typ) (V_{CC} = 2.5 V)
    : 1.5 µW (typ) (V_{CC} = 3.0 V)
- Completely static memory.
  - No clock or timing strobe required
- Equal access and cycle times
- Common data input and output.
  - Three state output
- Battery backup operation.
- Temperature range: –40 to +85°C

Ordering Information

Type No.	Access time	Package
R1LV0414CSB-5SI	55 ns	400-mil 44-pin plastic TSOP II (44P3W-H)
R1LV0414CSB-7LI	70 ns	

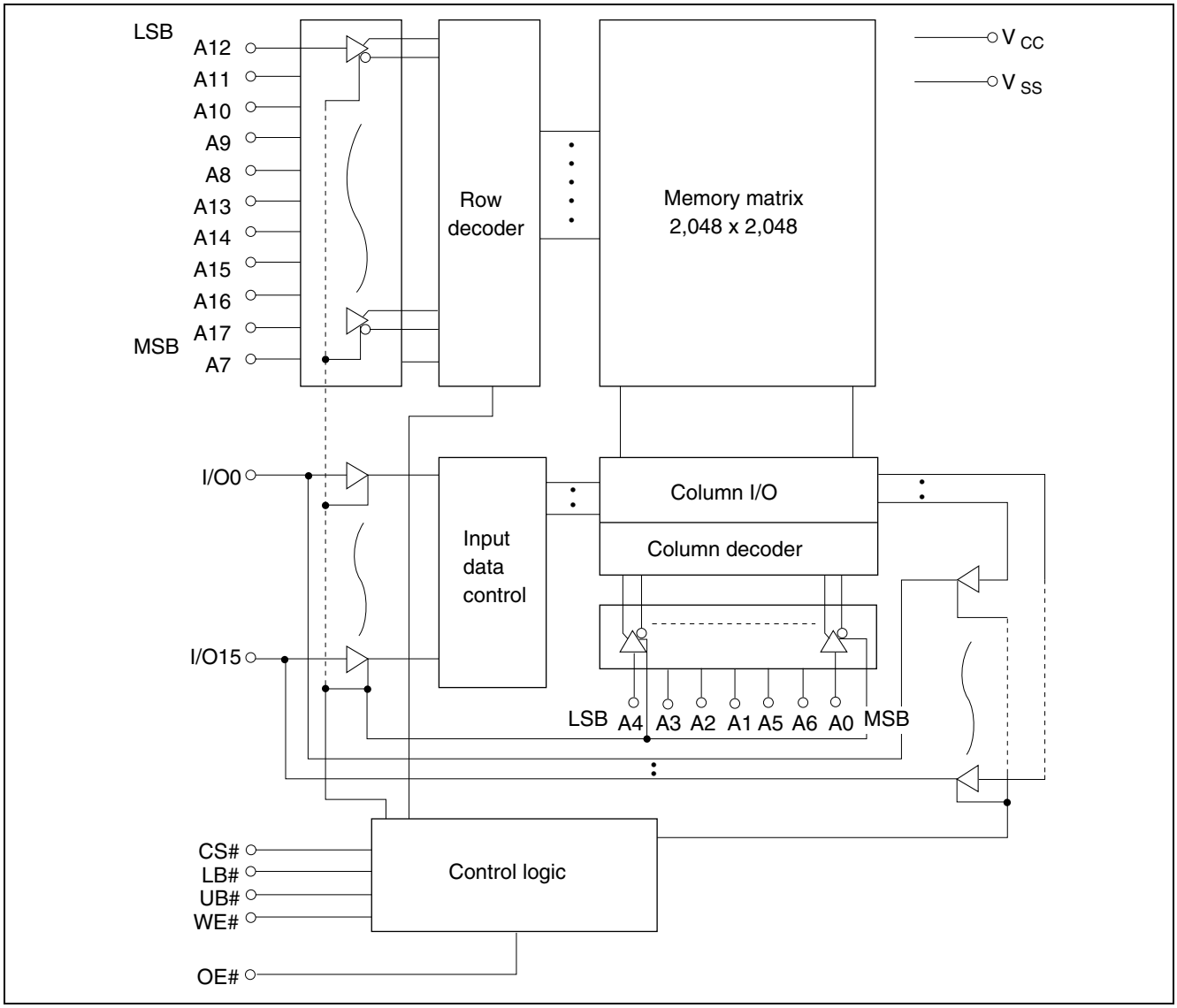
Pin Arrangement



Pin Description

Pin name	Function
A0 to A17	Address input
I/O0 to I/O15	Data input/output
CS# ($\overline{CS}$)	Chip select
OE# ($\overline{OE}$)	Output enable
WE# ($\overline{WE}$)	Write enable
LB# ($\overline{LB}$)	Lower byte select
UB# ($\overline{UB}$)	Upper byte select
V_{CC}	Power supply
V_{SS}	Ground
NC	No connection

Block Diagram



Operation Table

CS#	WE#	OE#	UB#	LB#	I/O0 to I/O7	I/O8 to I/O15	Operation
H	×	×	×	×	High-Z	High-Z	Standby
×	×	×	H	H	High-Z	High-Z	Standby
L	H	L	L	L	Dout	Dout	Read
L	H	L	H	L	Dout	High-Z	Lower byte read
L	H	L	L	H	High-Z	Dout	Upper byte read
L	L	×	L	L	Din	Din	Write
L	L	×	H	L	Din	High-Z	Lower byte write
L	L	×	L	H	High-Z	Din	Upper byte write
L	H	H	×	×	High-Z	High-Z	Output disable

Note: H: V_{IH}, L: V_{IL}, ×: V_{IH} or V_{IL}

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage relative to V_{SS}	V_{CC}	–0.5 to +4.6	V
Terminal voltage on any pin relative to V_{SS}	V_T	–0.5*[1] to V_{CC} + 0.3*[2]	V
Power dissipation	P_T	0.7	W
Operating temperature	Topr	–40 to +85	°C
Storage temperature range	Tstg	–65 to +150	°C
Storage temperature range under bias	Tbias	–40 to +85	°C

Notes: 1. V_T min: –3.0 V for pulse half-width ≤ 30 ns.
2. Maximum voltage is +4.6 V.

DC Operating Conditions

(Ta = –40 to +85°C)

Parameter		Symbol	Min	Typ	Max	Unit	Note
Supply voltage		V_{CC}	2.2	2.5/3.0	3.6	V	
		V_{SS}	0	0	0	V	
Input high voltage	V_{CC} = 2.2 V to 2.7 V	V_{IH}	2.0	—	V_{CC} + 0.3	V	
	V_{CC} = 2.7 V to 3.6 V	V_{IH}	2.2	—	V_{CC} + 0.3	V	
Input low voltage	V_{CC} = 2.2 V to 2.7 V	V_{IL}	–0.2	—	0.4	V	1
	V_{CC} = 2.7 V to 3.6 V	V_{IL}	–0.3	—	0.6	V	1

Note: 1. V_{IL} min: –3.0 V for pulse half-width ≤ 30 ns.

DC Characteristics

Parameter			Symbol	Min	Typ	Max	Unit	Test conditions
Input leakage current			$\|I_{LI}\|$	—	—	1	µA	Vin = V_{SS} to V_{CC}
Output leakage current			$\|I_{LO}\|$	—	—	1	µA	CS# = V_{IH} or OE# = V_{IH} or WE# = V_{IL} or LB# = UB# = V_{IH}, $V_{I/O}$ = V_{SS} to V_{CC}
Operating current			I_{CC}	—	5*[1]	20	mA	CS# = V_{IL}, Others = V_{IH}/V_{IL}, $I_{I/O}$ = 0 mA
Average operating current			I_{CC1}	—	8*[1]	25	mA	Min. cycle, duty = 100%, $I_{I/O}$ = 0 mA, CS# = V_{IL}, Others = V_{IH}/V_{IL}
			I_{CC2}	—	2*[1]	5	mA	Cycle time = 1 µs, duty = 100%, $I_{I/O}$ = 0 mA, CS# ≤ 0.2 V, V_{IH} ≥ V_{CC} – 0.2 V, V_{IL} ≤ 0.2 V
Standby current			I_{SB}	—	0.1*[1]	0.3	mA	CS# = V_{IH}
Standby current	–5SI	to +85°C	I_{SB1}	—	—	10	µA	Vin ≥ 0 V
		to +70°C	I_{SB1}	—	—	8	µA	(1) CS# ≥ V_{CC} – 0.2 V
		to +40°C	I_{SB1}	—	0.7*[2]	3	µA	(2) LB# = UB# ≥ V_{CC} – 0.2 V,
		to +25°C	I_{SB1}	—	0.5*[1]	3	µA	CS# ≤ 0.2 V
	–7LI	to +85°C	I_{SB1}	—	—	20	µA	
		to +70°C	I_{SB1}	—	—	16	µA	
		to +40°C	I_{SB1}	—	0.7*[2]	10	µA	
		to +25°C	I_{SB1}	—	0.5*[1]	10	µA	
Output high voltage	V_{CC} =2.2 V to 2.7 V		V_{OH}	2.0	—	—	V	I_{OH} = –0.5 mA
	V_{CC} =2.7 V to 3.6 V		V_{OH}	2.4	—	—	V	I_{OH} = –1 mA
	V_{CC} =2.2 V to 3.6 V		V_{OH2}	V_{CC} – 0.2	—	—	V	I_{OH} = –100 µA
Output low voltage	V_{CC} =2.2 V to 2.7 V		V_{OL}	—	—	0.4	V	I_{OL} = 0.5 mA
	V_{CC} =2.7 V to 3.6 V		V_{OL}	—	—	0.4	V	I_{OL} = 2 mA
	V_{CC} =2.2 V to 3.6 V		V_{OL2}	—	—	0.2	V	I_{OL} = 100 µA

Notes: 1. Typical values are at V_{CC} = 3.0 V, Ta = +25°C and specified loading, and not guaranteed.
2. Typical values are at V_{CC} = 3.0 V, Ta = +40°C and specified loading, and not guaranteed.

Capacitance

(Ta = +25°C, f = 1.0 MHz)

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	Note
Input capacitance	Cin	—	—	8	pF	Vin = 0 V	1
Input/output capacitance	$C_{I/O}$	—	—	10	pF	$V_{I/O}$ = 0 V	1

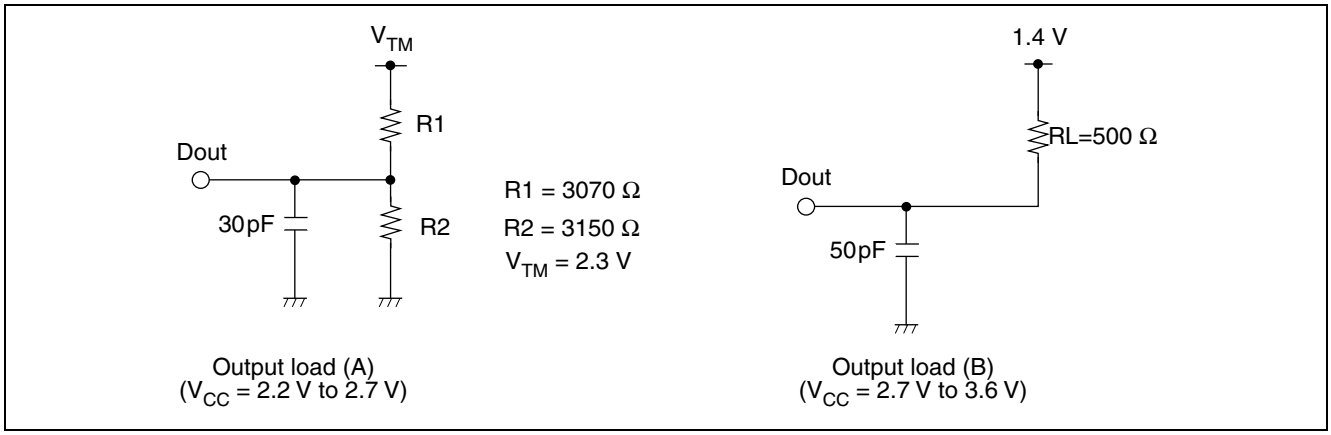
Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics

(Ta = –40 to +85°C, V_{CC} = 2.2 V to 3.6 V, unless otherwise noted.)

Test Conditions

- Input pulse levels: V_{IL} = 0.4 V, V_{IH} = 2.2 V (V_{CC} = 2.2 V to 2.7 V)
  : V_{IL} = 0.4 V, V_{IH} = 2.4 V (V_{CC} = 2.7 V to 3.6 V)
- Input rise and fall time: 5 ns
- Input/output timing reference levels: 1.1 V (V_{CC} = 2.2 V to 2.7 V)
  : 1.4 V (V_{CC} = 2.7 V to 3.6 V)
- Output load: See figures (Including scope and jig)



Read Cycle

Parameter	Symbol	R1LV0414C-I				Unit	Notes
		-5SI		-7LI			
		Min	Max	Min	Max		
Read cycle time	t_{RC}	55	—	70	—	ns	
Address access time	t_{AA}	—	55	—	70	ns	
Chip select access time	t_{ACS}	—	55	—	70	ns	
Output enable to output valid	t_{OE}	—	35	—	40	ns	
Output hold from address change	t_{OH}	10	—	10	—	ns	
LB#, UB# access time	t_{BA}	—	55	—	70	ns	
Chip select to output in low-Z	t_{CLZ}	10	—	10	—	ns	2, 3
LB#, UB# disable to low-Z	t_{BLZ}	5	—	5	—	ns	2, 3
Output enable to output in low-Z	t_{OLZ}	5	—	5	—	ns	2, 3
Chip deselect to output in high-Z	t_{CHZ}	0	20	0	25	ns	1, 2, 3
LB#, UB# disable to high-Z	t_{BHZ}	0	20	0	25	ns	1, 2, 3
Output disable to output in high-Z	t_{OHZ}	0	20	0	25	ns	1, 2, 3

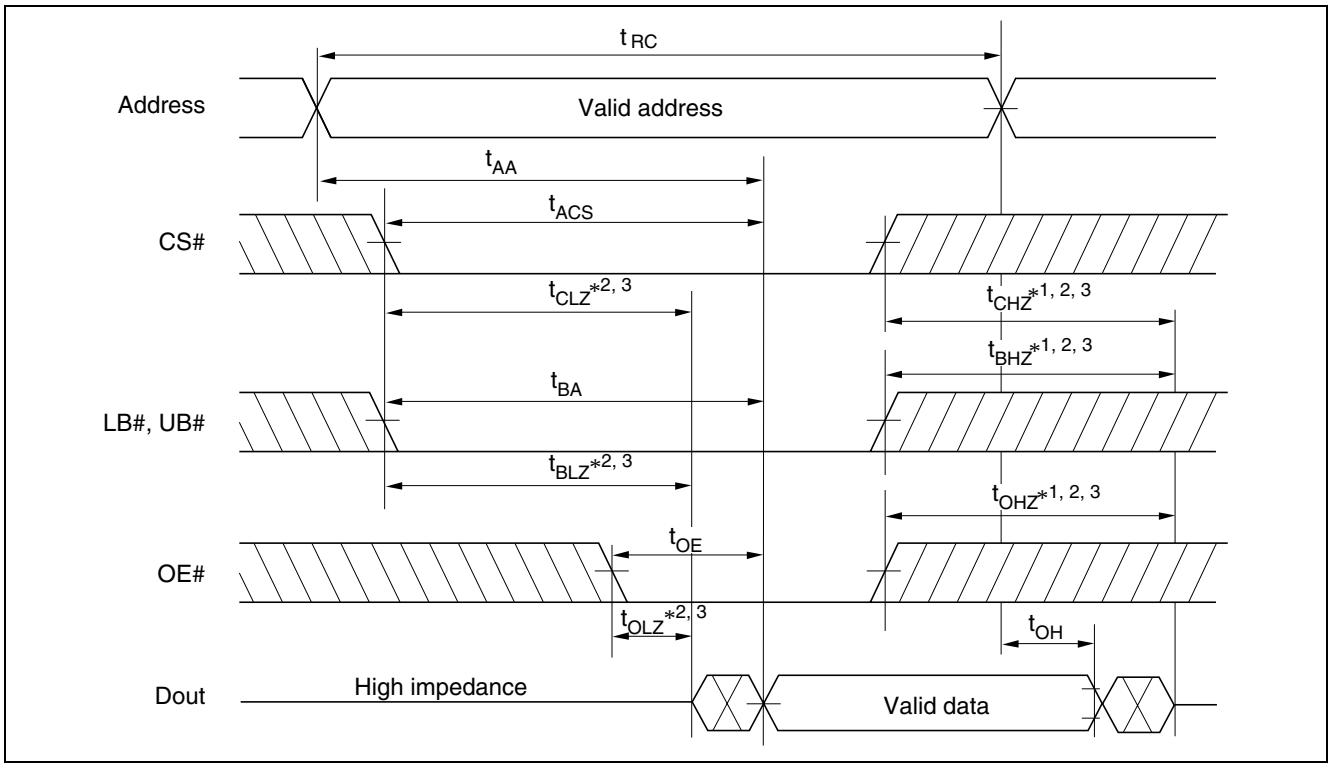
Write Cycle

Parameter	Symbol	R1LV0414C-I				Unit	Notes
		-5SI		-7LI			
		Min	Max	Min	Max		
Write cycle time	t_{WC}	55	—	70	—	ns	
Address valid to end of write	t_{AW}	50	—	60	—	ns	
Chip selection to end of write	t_{CW}	50	—	60	—	ns	5
Write pulse width	t_{WP}	40	—	50	—	ns	4
LB#, UB# valid to end of write	t_{BW}	50	—	55	—	ns	
Address setup time	t_{AS}	0	—	0	—	ns	6
Write recovery time	t_{WR}	0	—	0	—	ns	7
Data to write time overlap	t_{DW}	25	—	30	—	ns	
Data hold from write time	t_{DH}	0	—	0	—	ns	
Output active from end of write	t_{OW}	5	—	5	—	ns	2
Output disable to output in high-Z	t_{OHZ}	0	20	0	25	ns	1, 2, 3
Write to output in high-Z	t_{WHZ}	0	20	0	25	ns	1, 2

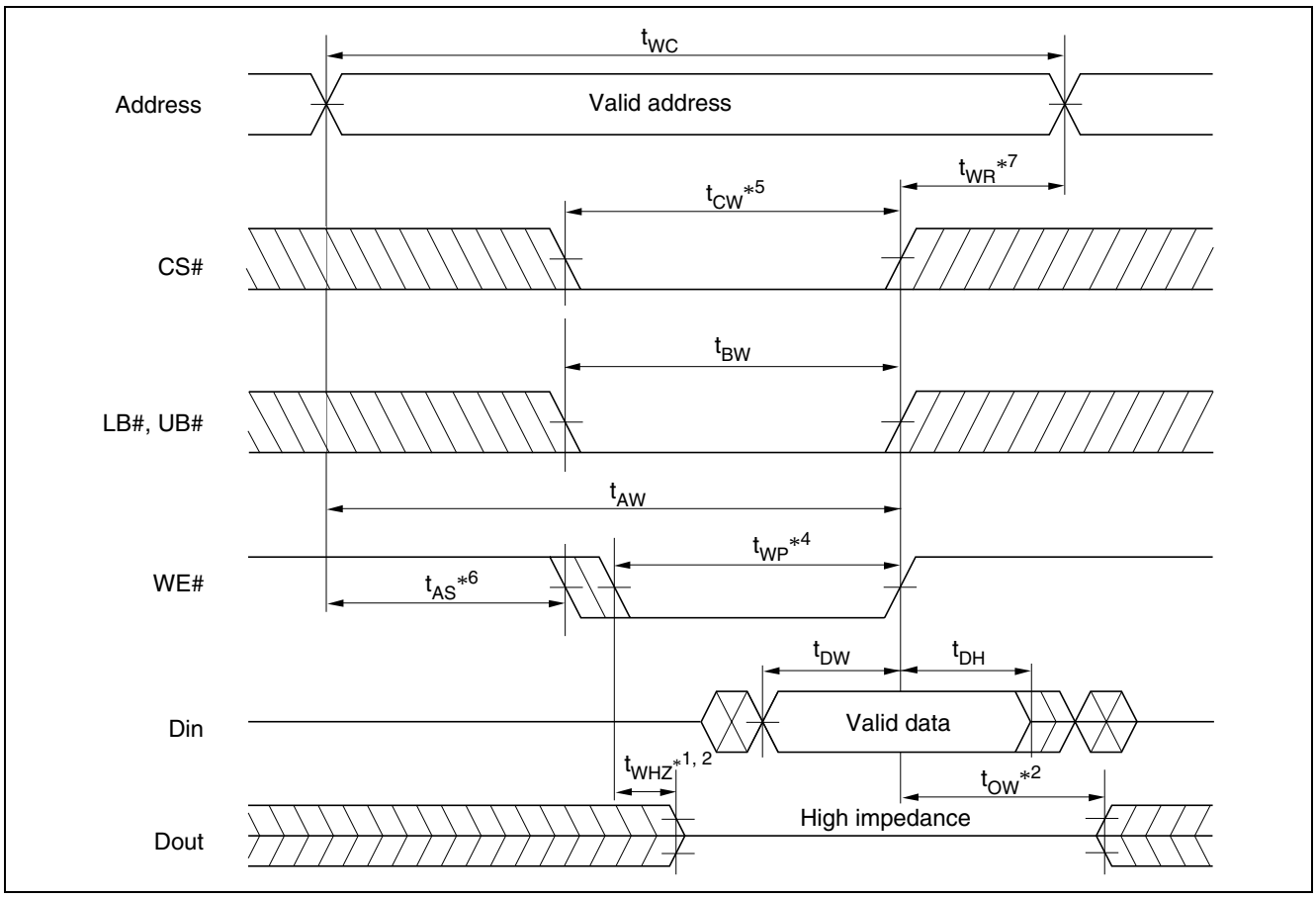
Notes:
1. t_{CHZ}, t_{OHZ}, t_{WHZ} and t_{BHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
2. This parameter is sampled and not 100% tested.
3. At any given temperature and voltage condition, t_{HZ} max is less than t_{LZ} min both for a given device and from device to device.
4. A write occures during the overlap of a low CS#, a low WE# and a low LB# or a low UB#. A write begins at the latest transition among CS# going low, WE# going low and LB# going low or UB# going low. A write ends at the earliest transition among CS# going high, WE# going high and LB# going high or UB# going high. t_{WP} is measured from the beginning of write to the end of write.
5. t_{CW} is measured from the later of CS# going low to the end of write.
6. t_{AS} is measured from the address valid to the beginning of write.
7. t_{WR} is measured from the earliest of CS# or WE# going high to the end of write cycle.

Timing Waveform

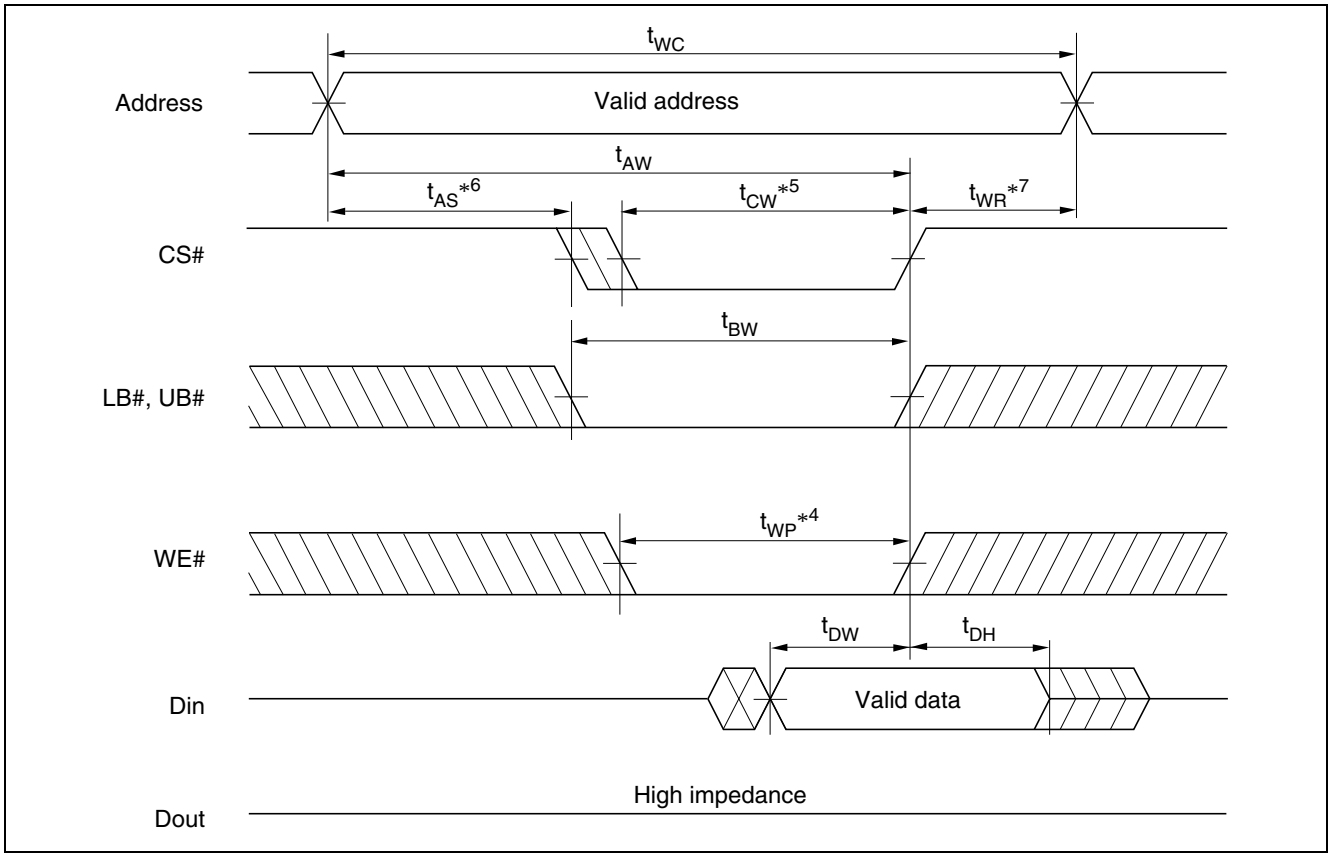
Read Timing Waveform (WE# = V_{IH})



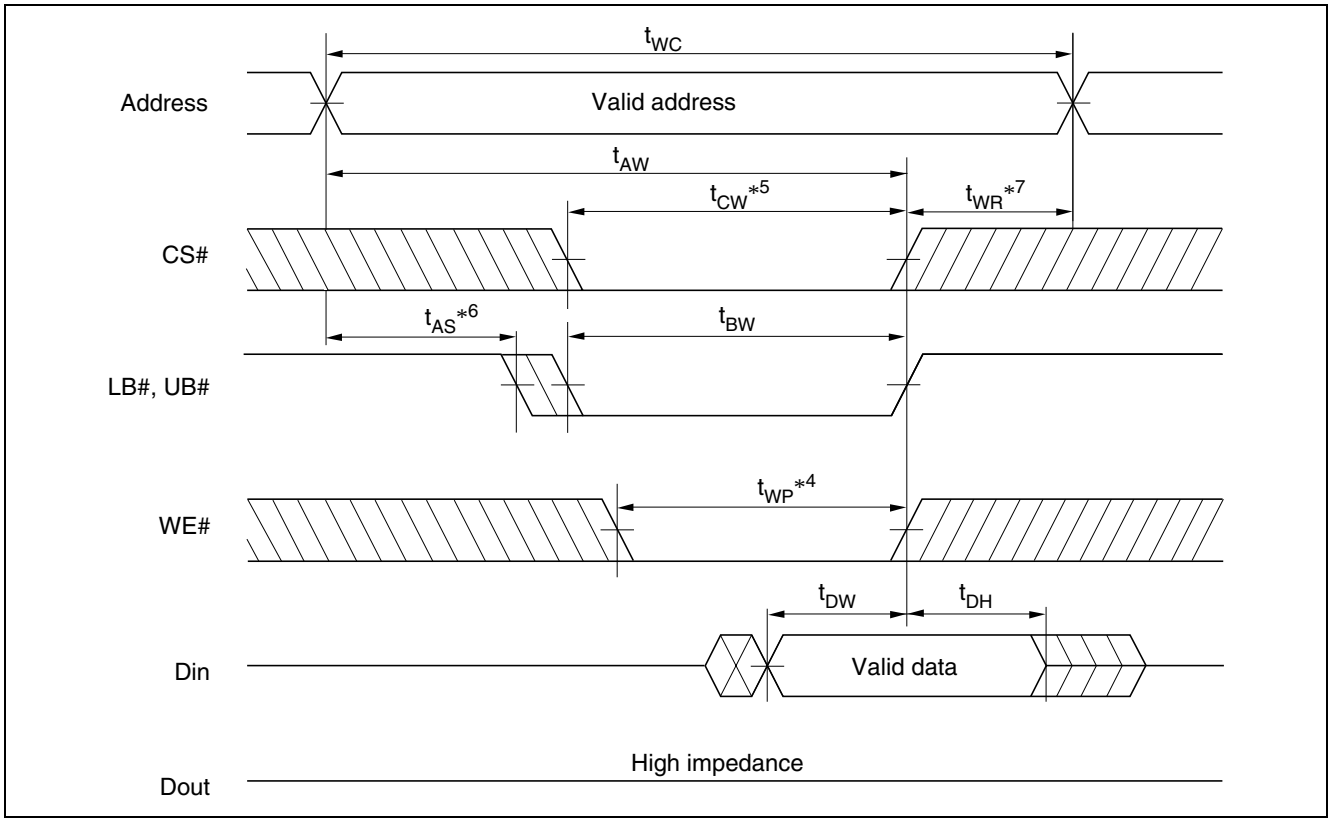
Write Timing Waveform (1) (WE# Clock)



Write Timing Waveform (2) (CS# Clock, OE# = V_{IH})



Write Timing Waveform (3) (LB#, UB# Clock, OE# = V_{IH})



Low V_{CC} Data Retention Characteristics

(Ta = –40 to +85°C)

Parameter			Symbol	Min	Typ	Max	Unit	Test conditions*[3]
V_{CC} for data retention			V_{DR}	2	—	—	V	Vin ≥ 0V (1) CS# ≥ V_{CC} – 0.2 V or (2) LB# = UB# ≥ V_{CC} – 0.2 V, CS# ≤ 0.2 V
Data retention current	–5SI	to +85°C	I_{CCDR}	—	—	10	µA	V_{CC} = 3.0 V, Vin ≥ 0V (1) CS# ≥ V_{CC} – 0.2 V or (2) LB# = UB# ≥ V_{CC} – 0.2 V, CS# ≤ 0.2 V
		to +70°C	I_{CCDR}	—	—	8	µA	
		to +40°C	I_{CCDR}	—	0.7*[2]	3	µA	
		to +25°C	I_{CCDR}	—	0.5*[1]	3	µA	
	–7LI	to +85°C	I_{CCDR}	—	—	20	µA	
		to +70°C	I_{CCDR}	—	—	16	µA	
		to +40°C	I_{CCDR}	—	0.7*[2]	10	µA	
		to +25°C	I_{CCDR}	—	0.5*[1]	10	µA	
Chip deselect to data retention time			t_{CDR}	0	—	—	ns	See retention waveform
Operation recovery time			t_R	t_{RC}*[4]	—	—	ns	

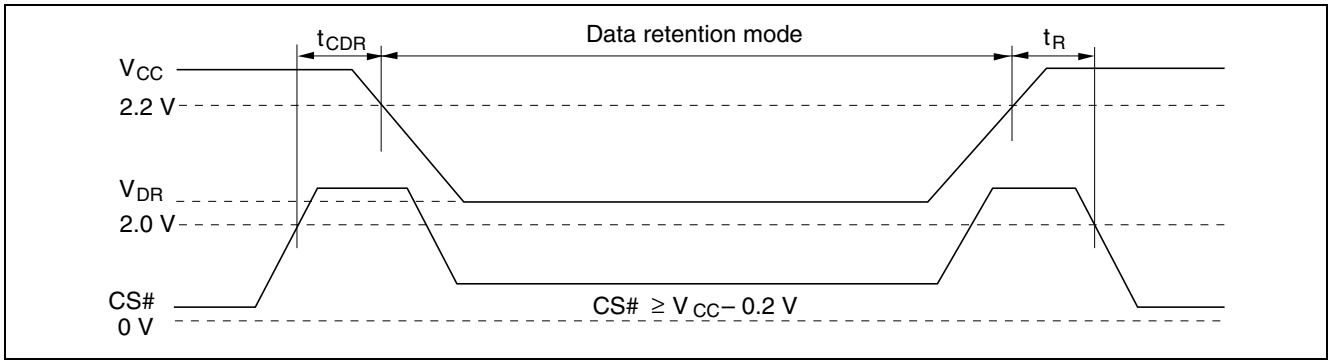
Notes: 1. Typical values are at V_{CC} = 3.0 V, Ta = +25°C and specified loading, and not guaranteed.

2. Typical values are at V_{CC} = 3.0 V, Ta = +40°C and specified loading, and not guaranteed.

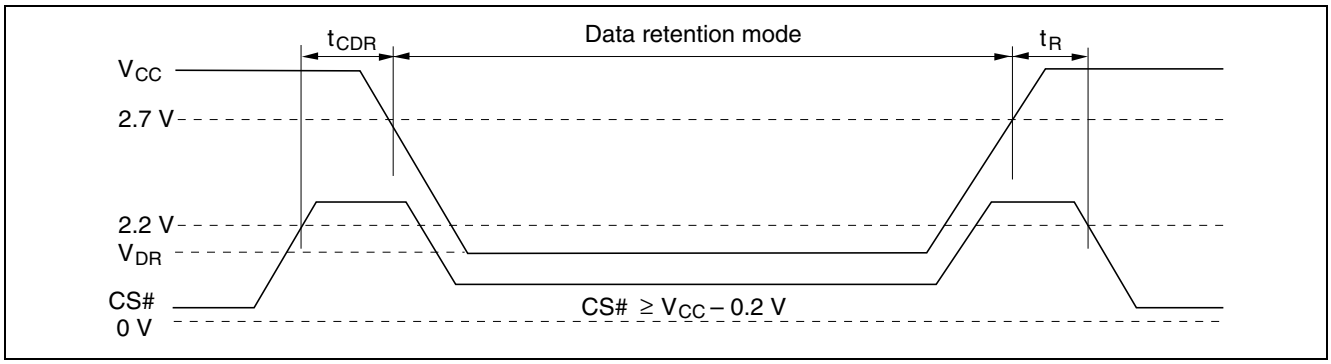
3. CS# controls address buffer, WE# buffer, OE# buffer, LB#, UB# buffer and Din buffer. If CS# controls data retention mode, Vin levels (address, WE#, OE#, LB#, UB#, I/O) can be in the high impedance state. If LB#, UB# controls data retention mode, LB#, UB# must be LB# = UB# ≥ V_{CC} – 0.2 V, CS# must be CS# ≤ 0.2 V. The other input levels (address, WE#, OE#, I/O) can be in the high impedance state.

4. t_{RC} = read cycle time.

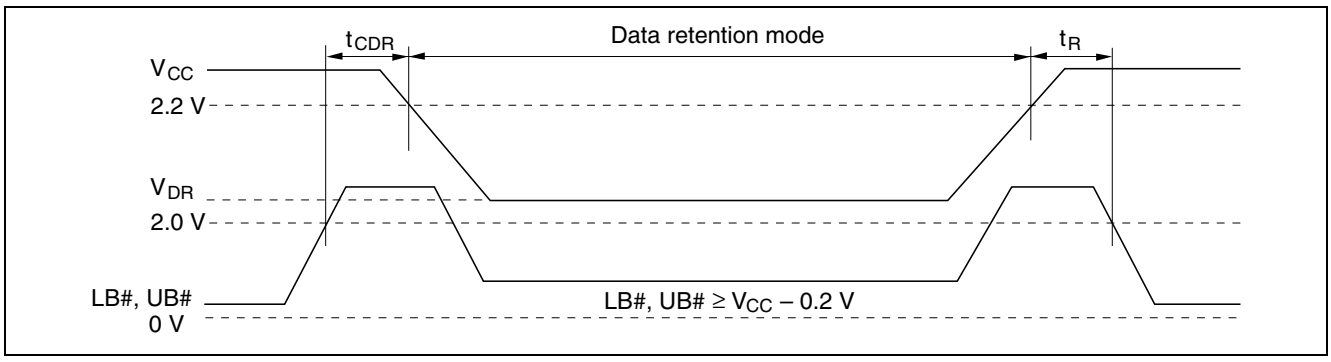
Low V_{CC} Data Retention Timing Waveform (1) (CS# Controlled) **(V_{CC} = 2.2 V to 2.7 V)**



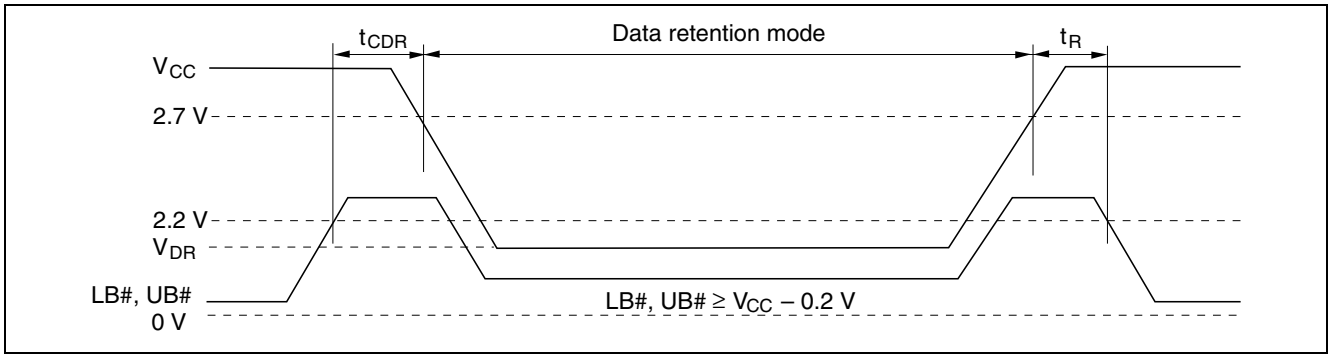
Low V_{CC} Data Retention Timing Waveform (2) (CS# Controlled) **(V_{CC} = 2.7 V to 3.6 V)**



Low V_{CC} Data Retention Timing Waveform (3) (LB#, UB# Controlled) **(V_{CC} = 2.2 V to 2.7 V)**



Low V_{CC} Data Retention Timing Waveform (4) (LB#, UB# Controlled) **(V_{CC} = 2.7 V to 3.6 V)**



Revision History	R1LV0414C-I Series Data Sheet

Rev.	Date	Contents of Modification	
		Page	Description
1.00	Mar. 10, 2004	—	Initial issue
2.00	May 26, 2004	5	Absolute Maximum Ratings Notes 2 : +7.0 V to +4.6 V
		6	DC characteristics –5SI and –7LI items' description are divided.
		7	AC characteristics
		8	Read Cycle/Notes: $t_{CLZ}/t_{BLZ}/t_{OLZ}$: Addition of [2, 3] $t_{CHZ}/t_{BHZ}/t_{OHZ}$: Addition of [1, 2, 3]
		9	Write Cycle/Notes: t_{OHZ} : Addition of [1, 2, 3]
		14	Low V_{CC} Data Retention Characteristics –5SI and –7LI items' description are divided. Low V_{CC} Data Retention Characteristics –5SI and –7LI items' description are divided.
2.01	Nov.24.2005	—	Change of format

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